

What is claimed is:

1. A method of preventing DRAM fuse sidewall from being eroded comprising steps of:
 - 5 forming a fuse on a substrate;
 - forming a dielectric layer on the substrate, said dielectric layer covering the fuse;
 - forming at least one work layer on the dielectric layer to constitute an intermediate structure;
 - forming a photoresist on the intermediate structure, and etching to form a fuse opening
 - 10 so that the fuse is exposed;
 - removing the photoresist;
 - forming a separate layer, said separate layer covering the exposed portion of the fuse at least; and
 - etching the separate layer to remove unnecessary portions thereof.
- 15 2. The method as recited in claim 1, wherein said separate layer, after its unnecessary portions are removed, covers the sidewall of the fuse at least.
3. The method as recited in Claim 1, wherein said separate layer uses SiN as its material.
4. The method as recited in Claim 1, wherein said separate layer uses SiON as its material.
5. The method as recited in Claim 1, further comprising a step of forming a protective layer
- 20 on the entire structure after the unnecessary portions of the separate layer are removed.
6. The method as recited in Claim 1, wherein said protective layer uses a polymer as its material.
7. A fuse structure manufactured according to Claim 1 or 2, which is characterized in that the sidewall of the fuse in the structure is covered with the separate layer.
- 25 8. The structure as recited in Claim 7, wherein said separate layer uses SiN as its material.
9. The structure as recited in Claim 7, wherein said separate layer uses SiON as its material.

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